

IN THE CLAIMS

Please amend claims 1, 2 and 10, cancel claims 11 and 12, and add new claim 13 as follows:

1. (CURRENTLY AMENDED) An integrated RF filter for use at microwave frequencies comprising:
 - an integrated circuit inductor with connected integrated circuit capacitors, arranged as a tank circuit, and an integrated circuit shunt resistor;
 - said inductor, capacitors and resistor being interconnected in a bridge-T filter arrangement;
 - and
 - each of said inductor, capacitors and resistor being a low-Q integrated element, yet wherein said integrated RF filter circuit results in a high-Q passive filter at microwave frequencies.
2. (CURRENTLY AMENDED) An integrated RF filter for use at microwave frequencies comprising:
 - first and second capacitors connected in series between an input and an output of said filter;
 - an inductor, connected between said input and said output of said filter, in parallel to said series connected capacitors, said first and second capacitors and said inductor comprising a tank circuit; and
 - a shunt resistor connected between ground, and the common side of said first and second capacitors;
 - each of said inductor, capacitors and resistor being a low-Q integrated element, yet wherein said integrated RF filter circuit results in a high-Q passive filter at microwave frequencies.
3. (ORIGINAL) The integrated RF filter of claim 2, wherein the value of said shunt resistor is selected to be equal in magnitude to the impedance of said inductor and capacitor tank circuit at the centre of its operating frequency band.
4. (ORIGINAL) The integrated RF filter of claim 2, wherein the value of said shunt resistor is selected to be equal in magnitude to the impedance of said inductor and capacitor tank circuit at its resonant frequency.

5. (PREVIOUSLY AMENDED) The integrated RF filter of claim 3, implemented in a silicon technology.

6. (ORIGINAL) The integrated RF filter of claim 3 wherein said silicon technology comprises silicon bipolar technology.

7. (ORIGINAL) Two or more integrated RF filters implemented according to claim 1, connected in a cascode arrangement, thereby enhancing their overall performance in providing additional rejection of out-of-band signals.

8. (ORIGINAL) The integrated RF filter of claim 5, wherein said capacitors are implemented as variable capacitors, thereby permitting a degree of tuning of the filter frequency of the circuit during use.

9. (ORIGINAL) The integrated RF filter of claim 8 wherein said variable capacitors are implemented using varactor diodes.

10. (CURRENTLY AMENDED) ~~As~~ The integrated RF filter as claimed in of claim 5, for use at frequencies exceeding wherein said center of said operating frequency exceeds 800 MHz.

11. (CANCELLED)

12. (CANCELLED)

13. (NEW) The integrated RF filter of claim 3, wherein the values of each of said inductor, capacitors and resistor are selected to provide a narrow band notch filter.